

Nancy Giles

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

73
papers

1,617
citations

20
h-index

39
g-index

73
ext. papers

1,724
ext. citations

2.5
avg, IF

4.58
L-index

#	Paper	IF	Citations
73	Cu ²⁺ and Cu ³⁺ acceptors in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals: A magnetic resonance and optical absorption study. <i>Journal of Applied Physics</i> , 2022 , 131, 065702	2.5	3
72	Electron traps in Ag-doped $\text{Li}_2\text{B}_4\text{O}_7$ crystals: The role of Ag interstitial ions. <i>Journal of Applied Physics</i> , 2022 , 131, 175106	2.5	1
71	Optically active selenium vacancies in BaGa_4Se_7 crystals. <i>Journal of Applied Physics</i> , 2021 , 130, 173104	2.5	1
70	Zn acceptors in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals. <i>Journal of Applied Physics</i> , 2021 , 129, 155701	2.5	11
69	Photoinduced trapping of charge at sulfur vacancies and copper ions in photorefractive $\text{Sn}_2\text{P}_2\text{S}_6$ crystals. <i>Journal of Applied Physics</i> , 2021 , 129, 085702	2.5	1
68	Near-infrared-sensitive photorefractive $\text{Sn}_2\text{P}_2\text{S}_6$ crystals grown by the Bridgman method. <i>Journal of Applied Physics</i> , 2020 , 127, 103103	2.5	4
67	Experimental determination of the $(0/\bar{1})$ level for Mg acceptors in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals. <i>Applied Physics Letters</i> , 2020 , 116, 142101	3.4	13
66	Charge trapping by iodine ions in photorefractive SnPS crystals. <i>Journal of Chemical Physics</i> , 2020 , 153, 144503	3.9	2
65	Deep donor behavior of iron in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals: Establishing the $\text{Fe}^{4+}/3+$ level. <i>Journal of Applied Physics</i> , 2020 , 128, 145704	2.5	7
64	Ir^{4+} ions in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals: An unintentional deep donor. <i>Journal of Applied Physics</i> , 2019 , 125, 045703	2.5	23
63	Deep donors and acceptors in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals: Determination of the $\text{Fe}^{2+}/3+$ level by a noncontact method. <i>Journal of Applied Physics</i> , 2019 , 126, 245701	2.5	24
62	Lithium and gallium vacancies in LiGaO_2 crystals. <i>Journal of Applied Physics</i> , 2018 , 124, 135702	2.5	7
61	Electron paramagnetic resonance and optical absorption study of acceptors in CdSiP_2 crystals. <i>AIP Advances</i> , 2018 , 8, 095014	1.5	2
60	Gallium vacancies in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals. <i>Applied Physics Letters</i> , 2017 , 110, 202104	3.4	88
59	Electron paramagnetic resonance study of neutral Mg acceptors in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals. <i>Applied Physics Letters</i> , 2017 , 111, 072102	3.4	42
58	Self-trapped holes in $\bar{\text{E}}\text{Ga}_2\text{O}_3$ crystals. <i>Journal of Applied Physics</i> , 2017 , 122, 215703	2.5	70
57	Interstitial silicon ions in rutile TiO_2 crystals. <i>Physical Review B</i> , 2015 , 91,	3.3	6

56	Oxygen vacancies in LiAlO ₂ crystals. <i>Physical Review B</i> , 2015 , 92,	3.3	10
55	Neutral nitrogen acceptors in ZnO: The ⁶⁷ Zn hyperfine interactions. <i>Journal of Applied Physics</i> , 2014 , 115, 103703	2.5	1
54	Triplet ground state of the neutral oxygen-vacancy donor in rutile TiO ₂ . <i>Physical Review B</i> , 2014 , 89,	3.3	20
53	Insertion of lithium ions into TiO ₂ (rutile) crystals: An electron paramagnetic resonance study of the Li-associated Ti ³⁺ small polaron. <i>Journal of Applied Physics</i> , 2013 , 113, 053712	2.5	19
52	Ground state of the singly ionized oxygen vacancy in rutile TiO ₂ . <i>Journal of Applied Physics</i> , 2013 , 114, 113702	2.5	20
51	Intrinsic small polarons in rutile TiO ₂ . <i>Physical Review B</i> , 2013 , 87,	3.3	75
50	Photoinduced EPR study of Sb ²⁺ ions in photorefractive Sn ₂ P ₂ S ₆ crystals. <i>Physical Review B</i> , 2012 , 86,	3.3	16
49	Hydrogen donors and Ti ³⁺ ions in reduced TiO ₂ crystals. <i>Journal of Applied Physics</i> , 2011 , 110, 053714	2.5	39
48	Oxygen vacancies adjacent to Cu ²⁺ ions in TiO ₂ (rutile) crystals. <i>Journal of Applied Physics</i> , 2011 , 109, 073711	2.5	19
47	Further characterization of oxygen vacancies and zinc vacancies in electron-irradiated ZnO. <i>Journal of Applied Physics</i> , 2008 , 103, 043710	2.5	116
46	Role of Neutral Impurity Scattering in the Analysis of Hall Data from ZnO and Other II-VI Materials. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 1035, 1		1
45	Persistent photoinduced changes in charge states of transition-metal donors in hydrothermally grown ZnO crystals. <i>Journal of Applied Physics</i> , 2007 , 101, 093706	2.5	42
44	Accurate measurement of composition, carrier concentration, and photoconductive lifetime in Hg _{1-x} Cd _x Te grown by molecular beam epitaxy. <i>Journal of Electronic Materials</i> , 2006 , 35, 1360-1368	1.9	6
43	Electron paramagnetic resonance and electron-nuclear double resonance study of Mn ²⁺ ions in CdGeAs ₂ crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 4070-4079	1.3	5
42	Optical properties of Cl-doped ZnSe epilayers grown on GaAs substrates. <i>Journal of Electronic Materials</i> , 2005 , 34, 944-948	1.9	
41	Thermal activation of beryllium-related photoluminescence by annealing of GaN grown by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2204-2207		12
40	Effect of growth conditions, surface orientation, and alloy composition on Cl incorporation and activation in ZnSe and Zn _{1-x} Mg _x Se grown by molecular beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005 , 23, 1814		1
39	Fundamental materials studies of undoped, In-doped, and As-doped Hg _{1-x} Cd _x Te. <i>Journal of Electronic Materials</i> , 2004 , 33, 728-736	1.9	25

38	Molecular beam epitaxy growth of high-quality arsenic-doped HgCdTe. <i>Journal of Electronic Materials</i> , 2004 , 33, 752-756	1.9	23
37	Determination of the ionization energy of nitrogen acceptors in zinc oxide using photoluminescence spectroscopy. <i>Applied Physics Letters</i> , 2004 , 84, 3049-3051	3.4	70
36	Determination of the Nitrogen Acceptor Ionization Energy in Zinc Oxide by Photoluminescence Spectroscopy. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 799, 251		
35	Luminescence study of ZnTe:Cr epilayers grown by molecular-beam epitaxy. <i>Journal of Electronic Materials</i> , 2003 , 32, 737-741	1.9	7
34	Thermal diffusion of lithium acceptors into ZnO crystals. <i>Journal of Electronic Materials</i> , 2003 , 32, 766-771	1.9	11
33	The path to ZnO devices: donor and acceptor dynamics. <i>Physica Status Solidi A</i> , 2003 , 195, 171-177		132
32	Temperature dependence of the free-exciton transition energy in zinc oxide by photoluminescence excitation spectroscopy. <i>Journal of Applied Physics</i> , 2003 , 94, 973-978	2.5	324
31	Thermal Activation of Beryllium in GaN Grown by RF-Plasma Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 798, 187		
30	Heavy Cr doping of ZnSe by molecular beam epitaxy. <i>Journal of Electronic Materials</i> , 2002 , 31, 770-775	1.9	18
29	Optical and EPR Study of Defects in Cadmium Germanium Arsenide. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 744, 1		
28	Luminescence and EPR Study of Lithium-Diffused ZnO Crystals. <i>Materials Research Society Proceedings</i> , 2002 , 744, 1		
27	The effect of high energy electrons during the growth of ZnSe and ZnMgSe by molecular beam epitaxy. <i>Journal of Electronic Materials</i> , 2001 , 30, 785-788	1.9	1
26	Sharp-line luminescence and absorption in ZnGeP ₂ . <i>Journal of Applied Physics</i> , 2001 , 90, 3314-3318	2.5	4
25	A Comparison of Magnesium and Beryllium Acceptors in GaN Grown by rf-Plasma Assisted Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 639, 331		7
24	Broad-band photoluminescence from ZnGeP ₂ . <i>Journal of Applied Physics</i> , 2000 , 87, 7310-7315	2.5	5
23	Absorption and photoluminescence spectroscopy of diffusion-doped ZnSe:Cr ²⁺ . <i>Journal of Electronic Materials</i> , 1999 , 28, 678-682	1.9	26
22	Characterization of defect-related optical absorption in ZnGeP ₂ . <i>Journal of Applied Physics</i> , 1999 , 86, 6677-6681	2.5	44
21	Photoluminescence excitation study of nitrogen-doped zinc selenide epilayers. <i>Journal of Applied Physics</i> , 1999 , 85, 6723-6727	2.5	3

20	Optical and EPR characterization of point defects in bismuth-doped CdWO ₄ crystals. <i>Radiation Effects and Defects in Solids</i> , 1999 , 149, 273-278	0.9	15
19	Photoluminescence and EPR of Phosphorus Vacancies in ZnGeP ₂ . <i>Materials Research Society Symposia Proceedings</i> , 1999 , 607, 445		4
18	Photoinduced Changes in the Charge States of Native Donors and Acceptors in ZnGeP ₂ . <i>Materials Research Society Symposia Proceedings</i> , 1999 , 607, 379		3
17	Nitrogen doping of ZnSe and CdTe epilayers: A comparison of two rf sources. <i>Journal of Electronic Materials</i> , 1998 , 27, 756-762	1.9	12
16	Point defects in Cd _{1-x} Zn _x Te: A correlated photoluminescence and EPR study. <i>Journal of Electronic Materials</i> , 1998 , 27, 813-819	1.9	10
15	Investigation of donor-acceptor pair luminescence from ZnSe:N epilayers. <i>Journal of Applied Physics</i> , 1998 , 84, 5743-5749	2.5	2
14	Hydrogenation of Undoped and Nitrogen Doped CdTe and ZnSe Grown by Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 513, 263		4
13	Compensating defects in heavily nitrogen-doped zinc selenide: A photoluminescence study. <i>Applied Physics Letters</i> , 1997 , 70, 1724-1726	3.4	9
12	Observation of singly ionized selenium vacancies in ZnSe grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1997 , 70, 2274-2276	3.4	29
11	PL and EPR Spectroscopy of Point Defects in Detector-Grade Cd _{1-x} Zn _x Te. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 487, 71		
10	Photoluminescence of nitrogen-doped zinc selenide epilayers. <i>Journal of Electronic Materials</i> , 1997 , 26, 732-737	1.9	2
9	The Effect of Hydrogen on the Molecular-Beam-Epitaxy Growth of GaN on Sapphire Under Ga-Rich Conditions. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 197		10
8	Photoluminescence and Electron Paramagnetic Resonance of Nitrogen-Doped Zinc Selenide Epilayers. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 442, 555		1
7	Photon assisted growth of nitrogen-doped CdTe and the effects of hydrogen incorporation during growth. <i>Journal of Electronic Materials</i> , 1996 , 25, 1247-1253	1.9	5
6	Band-Edge Photoluminescence at Room Temperature from ZnGeP ₂ and AgGaSe ₂ . <i>Physica Status Solidi (B): Basic Research</i> , 1996 , 198, 881-888	1.3	12
5	Electron Paramagnetic Resonance and Photoluminescence Studies of Point Defects in Zinc Germanium Phosphide (ZnGeP ₂). <i>Materials Research Society Symposia Proceedings</i> , 1996 , 450, 327		7
4	Photoluminescence and micro-Raman studies of as-grown and high-temperature-annealed KTiOPO ₄ . <i>Applied Physics Letters</i> , 1996 , 68, 897-899	3.4	7
3	Hydrogenation of undoped and nitrogen-doped CdTe grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1996 , 68, 529-531	3.4	29

- 2 Defect reduction in ZnSe grown by molecular beam epitaxy on GaAs substrates cleaned using atomic hydrogen. *Applied Physics Letters*, **1996**, 69, 82-84 3-4 35
- 1 Low-temperature photoluminescence from bulk CdTe and Cd_{0.967}Zn_{0.033}Te. *Journal of Applied Physics*, **1995**, 78, 1191-1195 2-5 14